

PSMN3R3-80BS

N-channel 80 V, 3.5 m Ω standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product data s

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	M	in Typ	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> -	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-5	5 -	175	°C
Static charact	eristics					
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{}$	-	3	3.5	mΩ
	resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.9	5 5.8	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14};$	-	28	-	nC
Q _{G(tot)}	total gate charge	see Figure 15		111	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 80 V; R_{GS} = 50 Ω ; unclamped	-	-	676	mJ

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EA)
mb	D	drain		
				mbb076 S
			∐ ∐ 1 3	
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PSMN3R3-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

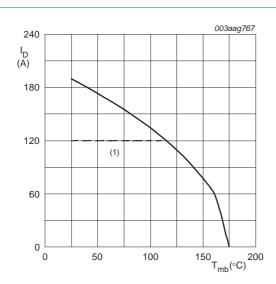
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mi	n Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20 \text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage		-20	0 20	V
I_D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } Figure 1$	<u>[1]</u> _	120	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> _	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	760	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	306	W
T _{stg}	storage temperature		-5	5 175	°C
Tj	junction temperature		-5	5 175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	[1] -	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	760	Α
Avalanche rug	gedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped	-	676	mJ

^[1] Continuous current is limited by package.

PSMN3R3-80BS

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 $V_{GS} \ge 10 \text{ V}$; (1) Capped at 120 A due to package

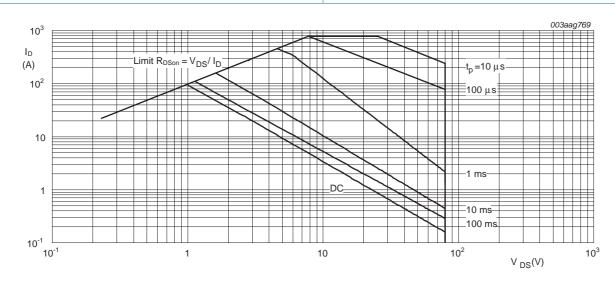
120
Pder (%)
80

40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

ig 2. Normalized total power dissipation as a

function of mounting base temperature





 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W

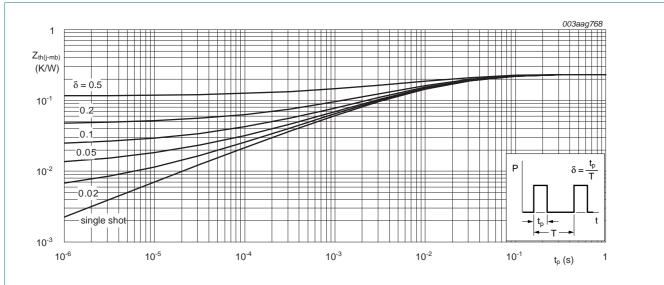


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
()	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10;see Figure 11	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
I_{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon} drain-source on-state resistance		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ;see <u>Figure 13</u>	-	7.1	8.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	3	3.5	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12;see Figure 13	-	4.95	5.8	mΩ	
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	104	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	111	-	nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 15	-	38	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	14	-	nC
Q_{GD}	gate-drain charge		-	28	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 75 A; V _{DS} = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.1	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8161	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	701	-	pF
C _{rss}	reverse transfer capacitance		-	337	-	pF
d(on)	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.53 \Omega; V_{GS} = 10 \text{ V};$	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A$	-	29	-	ns
t _{d(off)}	turn-off delay time		-	94	-	ns
t _f	fall time		-	33	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	59	-	ns
Q _r	recovered charge	V _{DS} = 20 V	-	109	-	nC

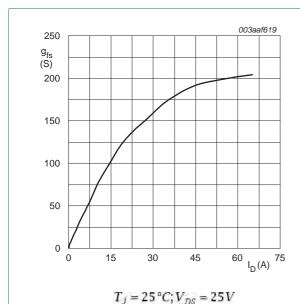


Fig 5. Forward transconductance as a function of drain current: typical values

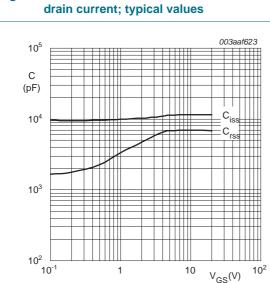
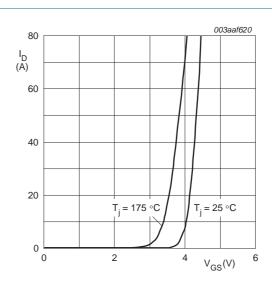


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$



 $V_{ extit{DS}}\!>\!I_{ extit{D}}\! imes\!R_{ extit{DSom}}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

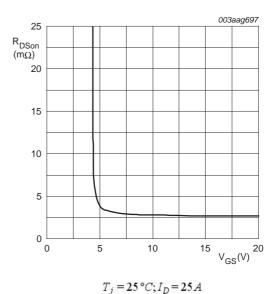
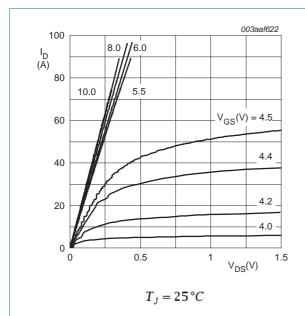


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



Output characteristics: drain current as a Fig 9. function of drain-source voltage; typical values

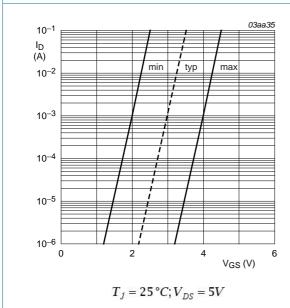
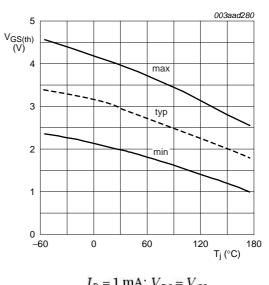


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

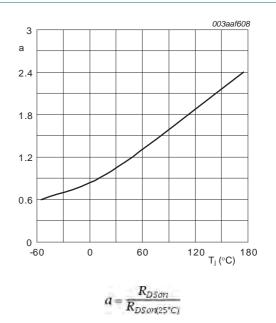


Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature

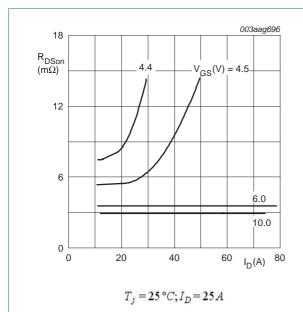


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

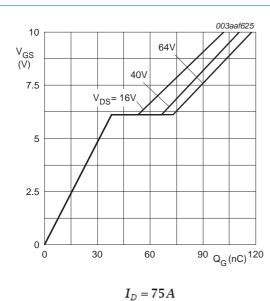


Fig 15. Gate-source voltage as a function of gate charge; typical values

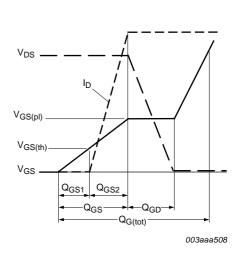
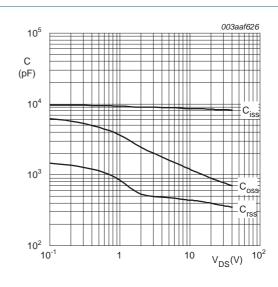
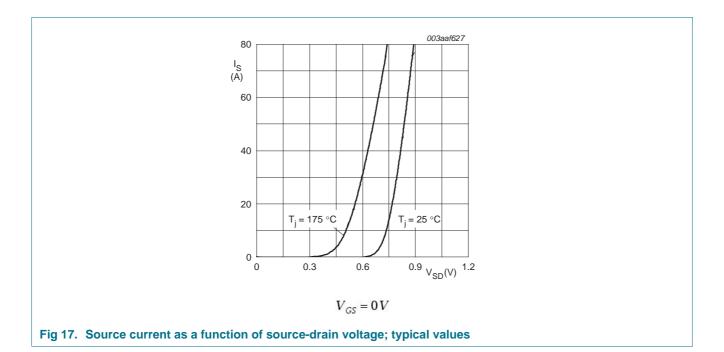


Fig 14. Gate charge waveform definitions



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

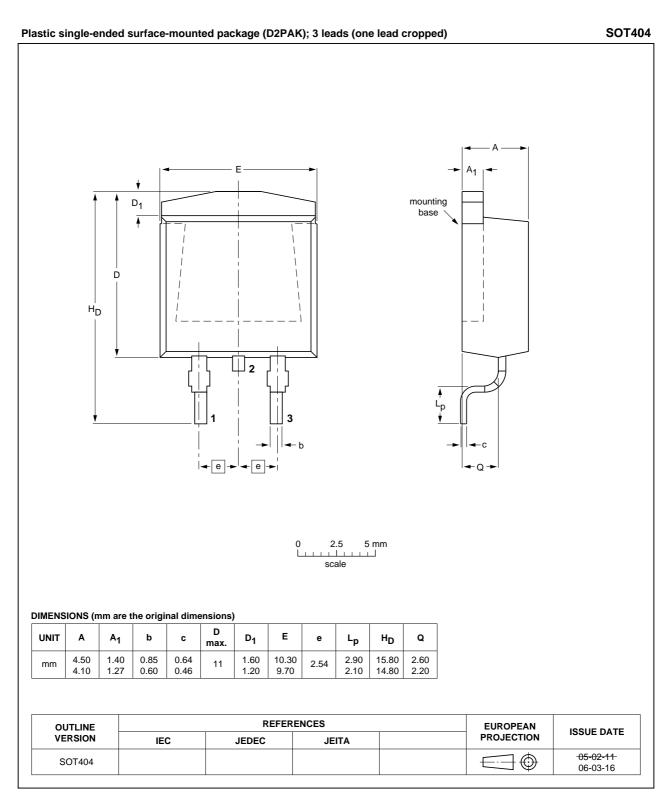


Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-80BS v.2	20120229	Product data sheet	-	PSMN3R3-80BS v.1
Modifications:	Status changedVarious changes	from objective to product. s to content.		
PSMN3R3-80BS v.1	20110928	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Nexperia PSMN3R3-80BS

N-channel 80 V, 3.5 mΩ standard level MOSFET in D2PAK

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